

ACTIVATION ENERGIES FROM CONDUCTIVITY-TEMPERATURE MEASUREMENTS*

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The experimental determination of activation energies in the electrical conductivity σ as a function of temperature is sometimes difficult, as the Arrhenius plot ($\log \sigma$ versus T^{-1}) may not be linear. This may be due to a process involving several similar activation energies, to conduction by polarons [1-3], or to variable range hopping of carriers [1,4]. In this paper we discuss a method of analysis of experimental results for $\log \sigma$ versus T^{-1} plots which helps to determine the best transport model [5,6], and which avoids an error which has appeared several times in the recent literature [7-9].

A general expression for dc electrical conductivity in semiconductors and in insulators is

$$\sigma(T) = A(T) \exp[-\beta W(T)], \quad (1)$$

where T is the temperature, $\beta^{-1} = k_B T$, k_B is the Boltzmann constant, and $A(T)$ and $W(T)$ are assumed to be slowly varying functions of the temperature. For example, several models of conduction [5,6] lead to $A(T) = aT^{-n}$. The usual analysis of the conduction curve by Arrhenius plot calculates the slope, or $W'(T)k_B^{-1}$ where

$$\begin{aligned} W'(T) &= -\partial \ln \sigma / \partial \beta \\ &= W(T) - \frac{\partial \ln A(T)}{\partial \beta} + \beta \frac{\partial W(T)}{\partial \beta}. \end{aligned} \quad (2)$$

If there is reason to believe that A and W are temperature independent, then the slope should be constant, yielding directly the activation energy, W . In the general case, knowledge of $W'(T)$ does not permit the two unknowns A and W to be uniquely determined. Often, however, models of electrical transport place additional constraints on the functions $A(T)$ and $W(T)$, and with these we can

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determine both from a knowledge of $\sigma(T)$. We illustrate this point with two model examples.

(1) *Variable range hopping.* Assuming a general function for the density of electronic states about the Fermi energy

$$N(E) = N_0(E - E_F)^p, \quad (4)$$

where

$$0 < p < \infty,$$

Hamilton [10] has shown that the dc electrical conductivity is related to this density of states by:

$$\sigma(T) = \sigma(0) \exp(-BT^{-1/(p+1)/(p+4)}), \quad (5)$$

Mott's widely quoted $T^{-1/4}$ law corresponds to the case $p=0$ and to a constant density of states near the Fermi energy [1,4]. An Arrhenius analysis [eq. (3)] yields the function

$$W'(T) = Bk_B \left(\frac{p+1}{p+4} \right) T^{3/(p+4)}. \quad (6)$$

The constants B and p may be independently determined by finding the intercept and the slope, respectively, on a $\log W'$ versus $\log T$ plot. The function $W'(T)$ also gives the hopping energy through the relation [10]

$$\Delta E = 2^{-p/(p+4)} W'. \quad (7)$$

This energy varies continuously from W' to $W'/2$ as p increases from 0 to a large value. Finally, as a check on the validity of this model, according to Mott [1,4] the energy W' must satisfy

$$W'(T) < 2^{p/(p+4)} k_B T. \quad (8)$$

(2) *Conduction by small polarons.* Schnakenberg (11) has analysed the non-adiabatic hopping energy W of small polarons at temperatures above $\theta_D/4$, where θ_D is the Debye temperature of the optical phonons of the solid, and he deduced the following high temperature relation:

$$W(T) = W_H \left(\frac{\tanh(\theta_D/4T)}{(\theta_D/4T)} \right) + \frac{W_D}{2}, \quad (9)$$

where W_D and W_H are two constants (disorder energy and high temperature small polaron hopping energy, respectively). Moreover, the conductivity $\sigma(T)$ is given by eq. (1), with the above expression for $W(T)$ and a prefactor, A , which is constant or depends only very weakly on temperature. Fitting the constants of the model using an Arrhenius plot analysis, this involves the energy

$$W''(T) = W_H \operatorname{sech}^2(\theta_D/4T) + W_D/2. \quad (10)$$

We determine the parameters W_H , W_D and θ_D in a two step process. First

we assume that W_D is zero and plot W'' versus T^{-2} for those temperatures. The values for W_H and W_D from the W'' versus $\operatorname{sech}^2(\theta_D/4T)$ plot are determined using eq. (9). Results are shown in fig. 1. Results are in good agreement with those determined using eq. (9). Results are in good agreement with those determined using eq. (9). Results are in good agreement with those determined using eq. (9).

As an example of the analysis of the data for the models just described to the case of mica [12,13]. Applying the variable range hopping model is linearly dependent upon $T^{-1/4}$ at low temperature. However, the relation [8]. In addition, the results are in good agreement with those determined using eq. (9). Results are in good agreement with those determined using eq. (9). Results are in good agreement with those determined using eq. (9).

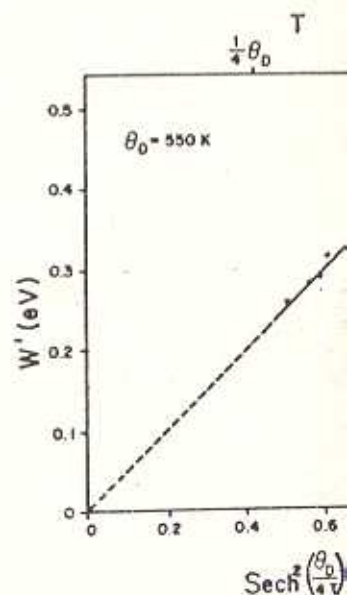


Fig. 1. Best fit of the small polaron hopping energy W'' versus $\operatorname{sech}^2(\theta_D/4T)$ for mica as shown by a plot of W'' versus $\operatorname{sech}^2(\theta_D/4T)$. $W_H = 0.5$ eV, $W_D = 0.0$ eV and $\theta_D = 550$ K.

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we assume that W_D is zero and calculate θ_D and W_H from the slope of a W'' versus T^{-2} plot for those temperatures above $\theta_D/4$. Second we find better values for W_H and W_D from the slope and the intercept of the straight line in a W'' versus $\text{sech}^2(\theta_D/4T)$ plot. The hopping energy $W(T)$ may then be determined using eq. (9). Recently, several authors [7-9] have made the mistake of calculating θ_D from eq. (9), instead of eq. (10) for $W''(T)$, in the analyses of their Arrhenius plots. This leads to values of the Debye temperature θ_D which are a factor of up to 2 too large.

As an example of the analyses described above, we have applied the two models just described to the conductivity-temperature data for biotite mica [12,13]. Applying the variable range hopping model, we indeed find that $\log \sigma$ is linearly dependent upon T at high temperature, and varies roughly as $T^{1/4}$ at low temperature. However, $W(T)$ thus obtained does not satisfy the relation [8]. In addition, the resulting values of W'' and of B lead to unreasonable values for the hopping length and of the density of states at the Fermi energy [12]. In contrast, use of the small polaron model to calculate $W''(T)$ yields physically plausible values, $W_H = 0.5$ eV, $W_D = (0 \pm 0.05)$ eV and $\theta_D = 550$ K. In fig. 1 we show the fit of $W''(T)$ versus $\text{sech}^2(\theta_D/4T)$, using these values of the parameters. The excellent fit supports both the methodology for the parameters, as well as the model of conduction in biotite mica.

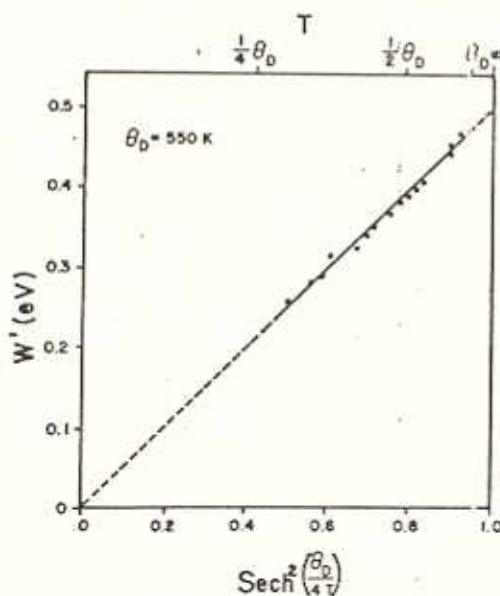


Fig. 1. Best fit of the small polaron hopping model to conductivity-temperature data for biotite mica as shown by a plot of $W''(T)$ versus $\text{sech}^2(\theta_D/4T)$. The values of the parameters are $W_H = 0.5$ eV, $W_D = 0.0$ eV and $\theta_D = 550$ K.

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LOW-TEMPERATURE THERMAL CONDUCTIVITY OF VYCOR

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Measurements [1] of the low-temperature thermal conductivity of amorphous polymers have shown a strong and explicit frequency dependence and that this frequency dependence is characteristic of a dispersive "plateau" (roughly temperature independent) in amorphous materials. This conclusion is supported by [2,3]. In brief, the strong frequency dependence of the thermal conductivity of amorphous materials serves as low-pass filters for phonons. At 30 K, the heat is carried by phonons with a mean free path of ≈ 1 K rather than 30 K. The thermal conductivity of amorphous materials is therefore limited by the scattering of phonons by the thermal conductivity of amorphous materials, $d < \lambda$. If indeed long-wavelength phonons were available only for temperatures above 100 K, the thermal conductivity of amorphous materials would be much higher [5] to 100 K, and for two different papers is to determine if the measurements are correct.

Porous Vycor is produced by leaching silica from a silica glass. The remaining phase is a porous silica structure with a pore size from 35 to 75 Å in diameter. The available thermal conductivity of porous Vycor is shown in fig. 1 are data for silica glass. The values of d and r for the porous Vycor are shown in fig. 1 are data for silica glass.

The plan is to obtain a frequency dependence of the thermal conductivity of the vitreous silica data, then compare it with the Vycor data to see if the Vycor data can be explained by the same mechanism.

* The comment in section 4 of ref. [1] that the frequency dependence of the measurements is not correct.